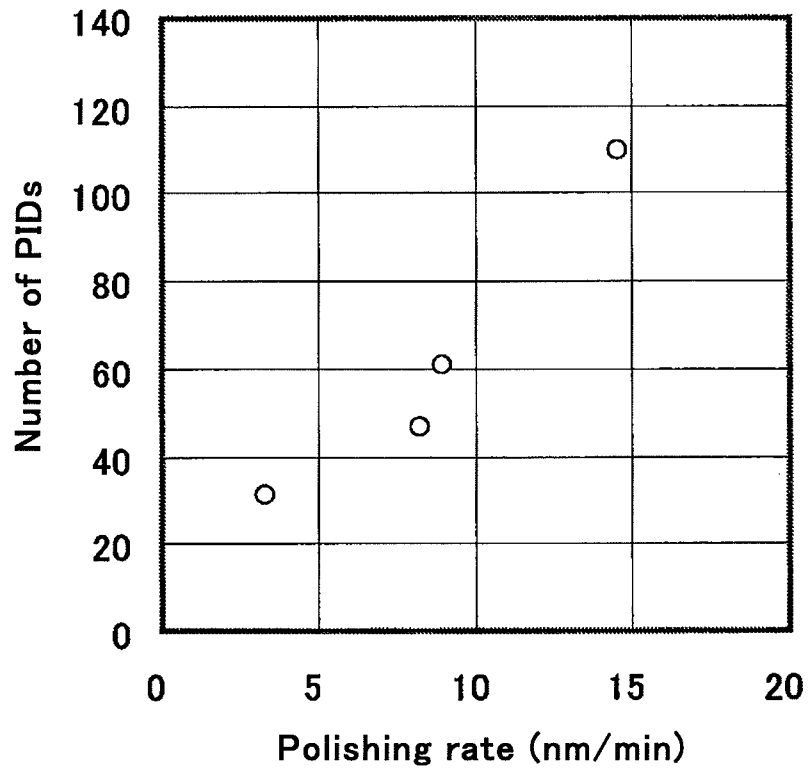
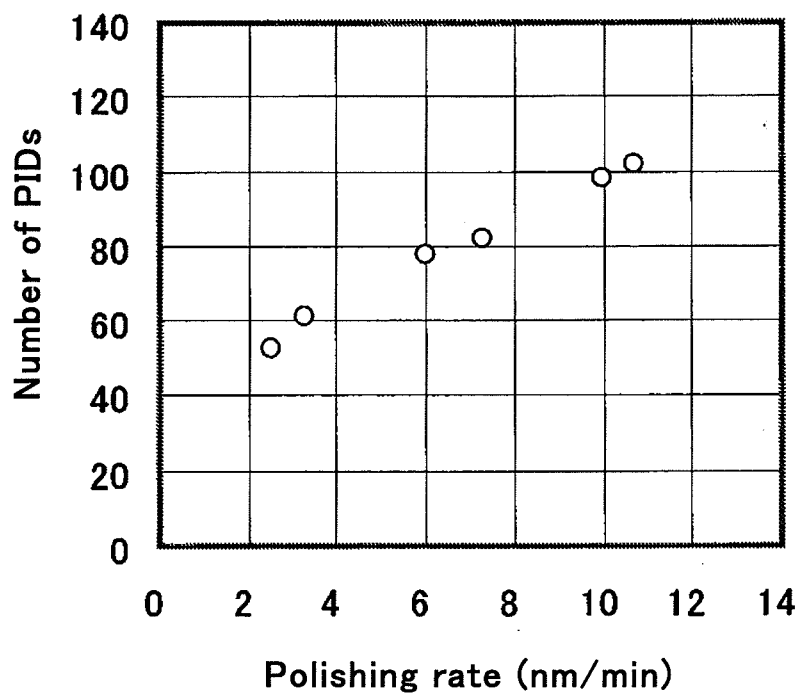


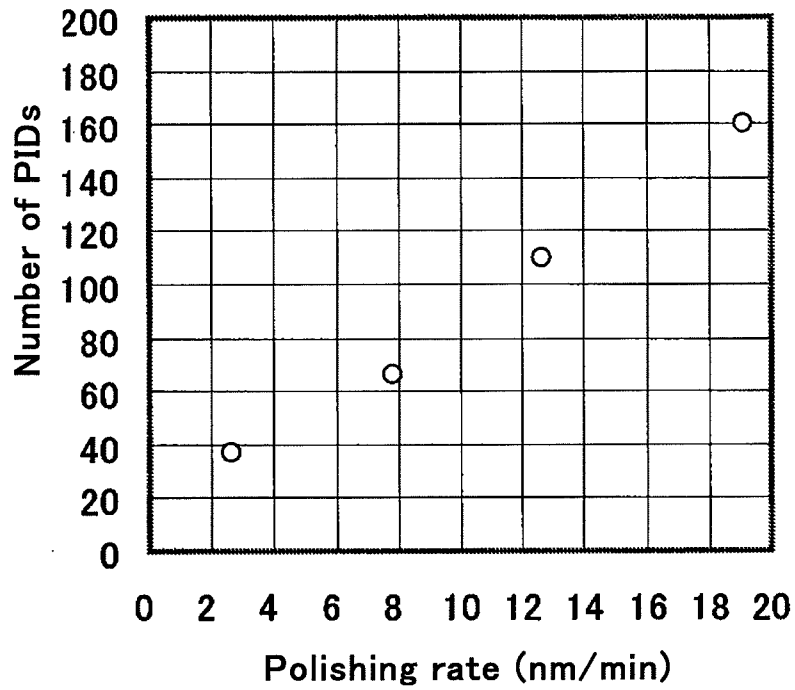
[Fig. 1]



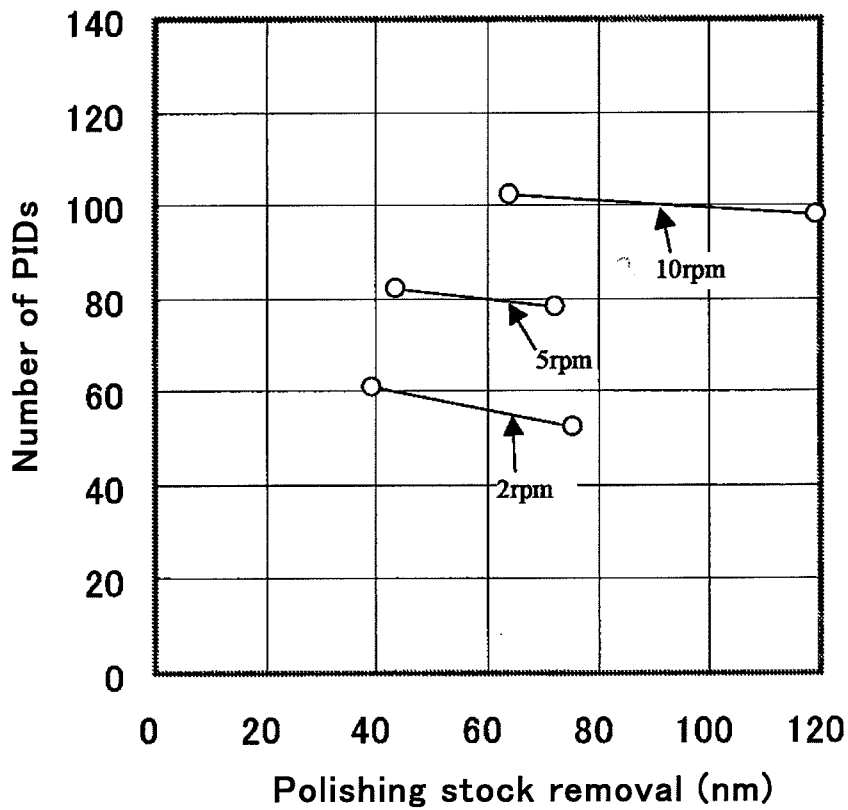
[Fig. 2]



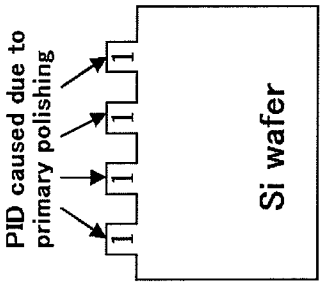
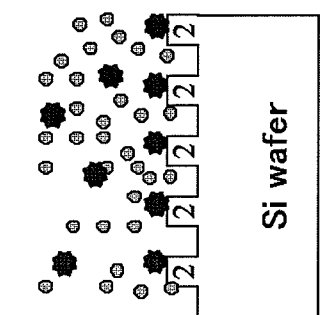
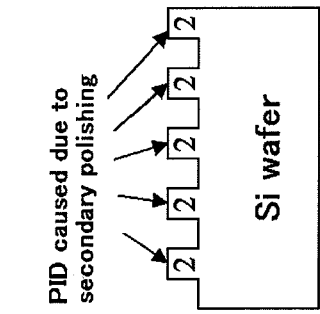
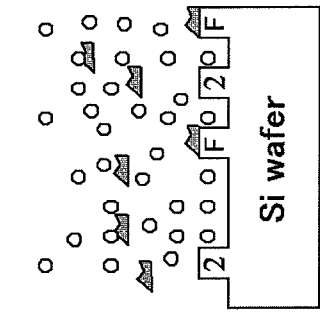
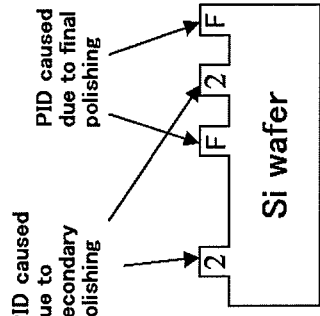
[Fig. 3]



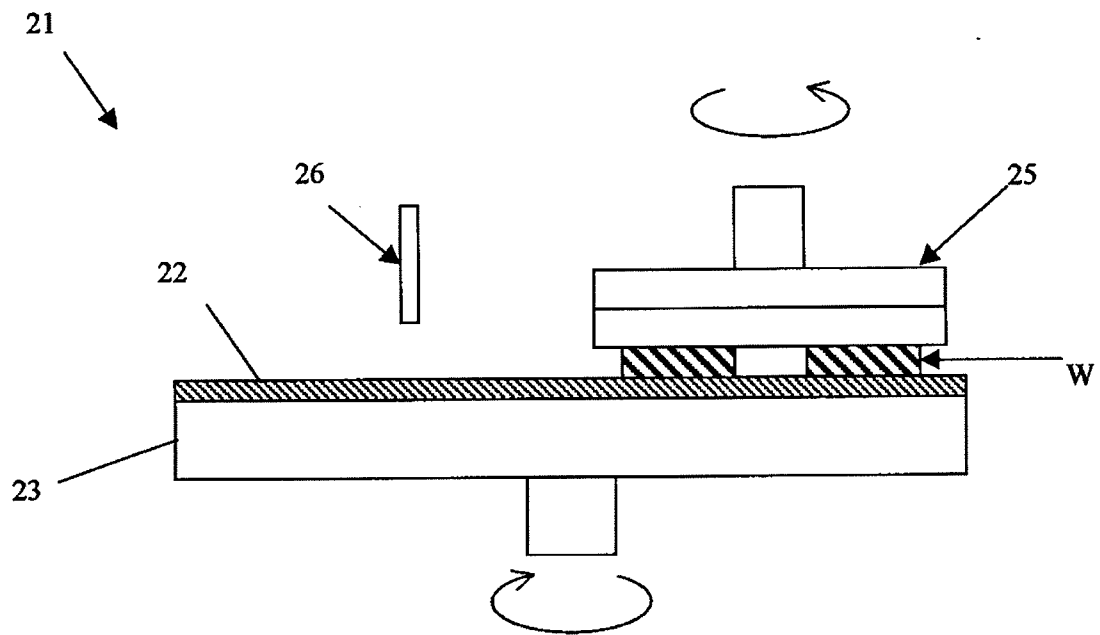
[Fig. 4]



[Fig. 5]

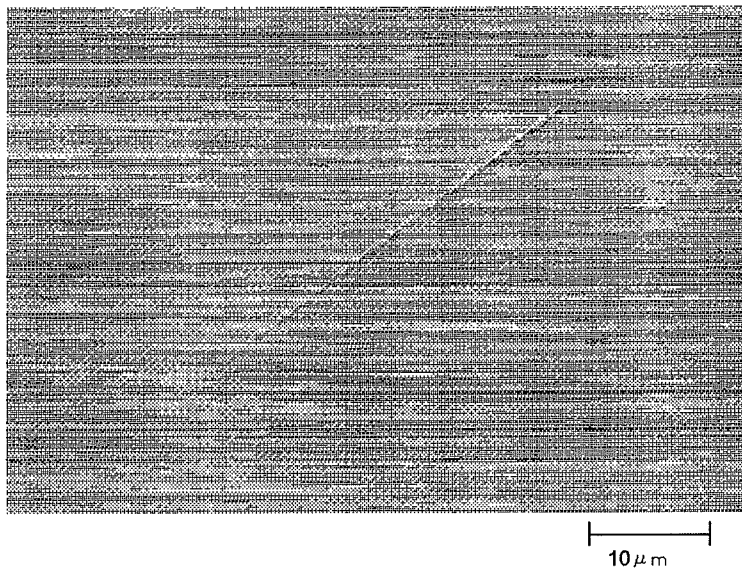
(a)	(b)	(c)	(d)	(e)
After primary polishing	During secondary polishing Particle for polishing ○ Foreign matter ⊛	After secondary polishing	During final polishing Particle for polishing ○ Foreign matter ⊛	After final polishing
 PID caused due to primary polishing Si wafer	 PID caused due to secondary polishing Si wafer	 PID caused due to secondary polishing Si wafer	 PID caused due to secondary polishing PID caused due to final polishing Si wafer	 PID caused due to secondary polishing PID caused due to final polishing Si wafer

[Fig. 6]

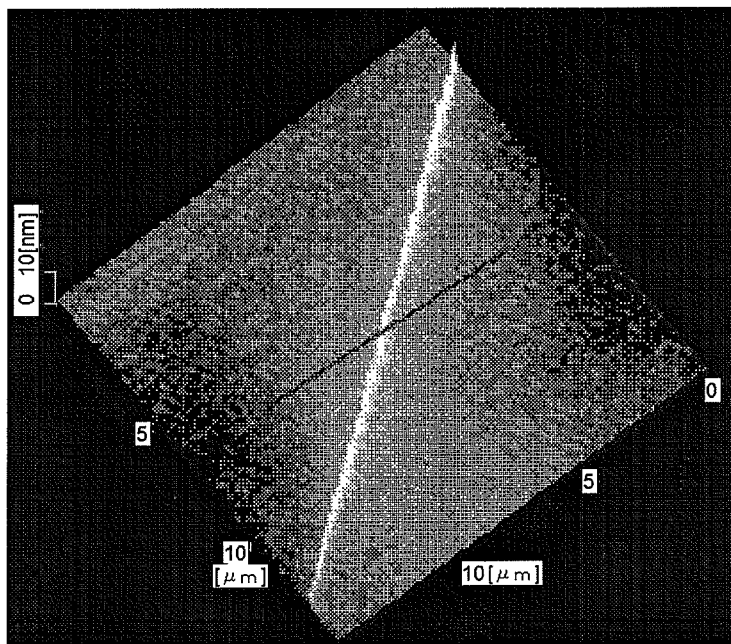


[Figs. 7]

(a)



(b)



(c)

